

Magnetization reversal by electric field in Co substituted BiFeO₃

Masaki Azuma^{1,2}, Kei Shigematsu^{1,2}, Hajime Hojo³, Keisuke Shimizu¹,
Takuma Itoh¹, Ko Mibu⁴

¹ *Laboratory for Materials and Structures, Tokyo Institute of Technology, Japan*

² *Kanagawa Institute of Industrial Science and Technology, Japan*

³ *Department of Energy and Material Science, Kyushu University, Japan*

⁴ *Nagoya Institute of Technology, Japan*

Electric field manipulation of magnetization is intensively investigated because of potential application in low-power-consumption non-volatile magnetic memory devices. Ferroelectric BiFeO₃ has a cycloidal space-modulated spin structure with a periodicity of 62 nm superimposed on the G-type antiferromagnetic structure which prohibits the appearance of net ferromagnetic magnetization due to spin canting. We have observed a spin structure transition from low-temperature cycloidal one to high-temperature collinear one with at ~200 K using Mössbauer spectroscopy in rhombohedral BiFe_{0.1}Co_{0.9}O₃ thin films fabricated by PLD on SrTiO₃ (STO) (111) substrate [1, 2]. Spontaneous magnetization of 0.03 u_B/f.u. confined in a magnetic easy plane perpendicular to the electric polarization is generated by Dzyaloshinskii-Moriya interaction. Films fabricated on GdScO₃ (110) substrate has out-of-plane component of magnetization which can be observed by magnetic force microscopy (MFM). It is demonstrated that the out-of-plane magnetization can be reversed by electric polarization reversal using piezoresponse force microscopy (PFM) at room temperature [3, 4] while the magnetization reversal is absent when the polarization reversal is in-plane [5].

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